

## Product Summary

$BV_{DSS}$	$R_{DS(ON)} \text{ Max}$	$I_D$ $T_C = +25^\circ\text{C}$ (Note 9)
60V	3.4mΩ @ $V_{GS} = 10V$	100A

## Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

## Applications

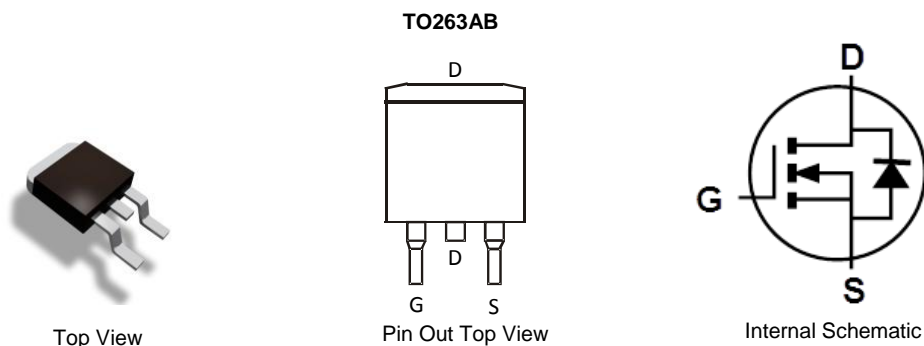
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

## Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low  $R_{DS(ON)}$  – Minimizes Power Losses
- Low  $Q_g$  – Minimizes Switching Losses
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([DMTH6004SCTBQ](#))**

## Mechanical Data

- Case: TO263AB
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 1.7 grams (Approximate)

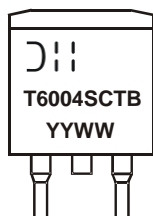


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH6004SCTB-13	TO263AB	800 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



T6004SCTB = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 15 = 2015)  
 WW = Week (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	60	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6)	I <sub>D</sub>	T <sub>C</sub> = +25°C (Note 9)	100
		T <sub>C</sub> = +100°C	100
Maximum Continuous Body Diode Forward Current (Note 6)	I <sub>S</sub>	100	A
Pulsed Drain Current (10µs Pulse, Duty Cycle=1%)	I <sub>DM</sub>	200	A
Avalanche Current, L=0.2mH	I <sub>AS</sub>	45	A
Avalanche Energy, L=0.2mH	E <sub>AS</sub>	200	mJ

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	4.7	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	32	°C/W
Total Power Dissipation (Note 6)	P <sub>D</sub>	136	W
Thermal Resistance, Junction to Case (Note 6)	R <sub>θJC</sub>	1.1	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	—	4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	2.9	3.4	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 100A
Diode Forward Voltage	V <sub>SD</sub>	—	—	1.3	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 100A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>ISS</sub>	—	4,556	—	pF	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V f = 1MHz
Output Capacitance	C <sub>OSS</sub>	—	1,383	—		
Reverse Transfer Capacitance	C <sub>RSS</sub>	—	105.2	—		
Gate Resistance	R <sub>g</sub>	—	0.66	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	—	95.4	—	nC	V <sub>DD</sub> = 30V, I <sub>D</sub> = 90A, V <sub>GS</sub> = 10V
Gate-Source Charge	Q <sub>gs</sub>	—	21.6	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	20.4	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	13.2	—	ns	V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 90A, R <sub>G</sub> = 3.5Ω
Turn-On Rise Time	t <sub>r</sub>	—	11.7	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	31	—		
Turn-Off Fall Time	t <sub>f</sub>	—	12	—		
Reverse Recovery Time	t <sub>RR</sub>	—	50.5	—	ns	I <sub>F</sub> = 50A, di/dt = 100A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	—	80.8	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
  - Thermal resistance from junction to soldering point (on the exposed drain pad).
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.
  - Package limited.

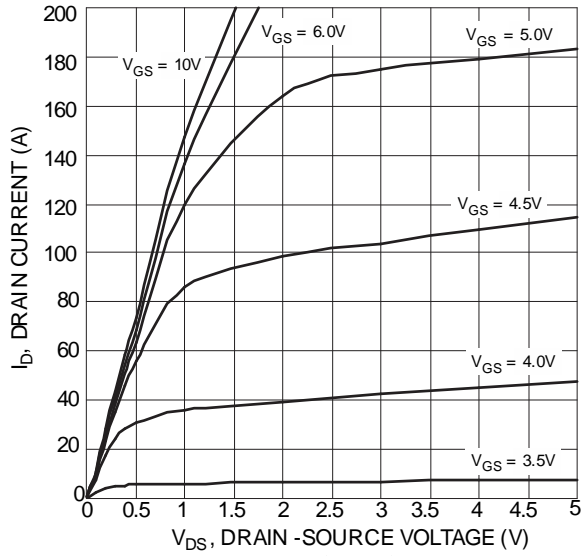


Figure 1 Typical Output Characteristics

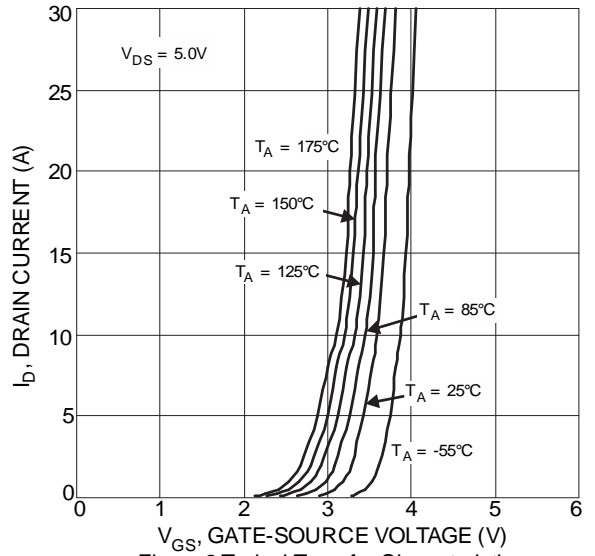


Figure 2 Typical Transfer Characteristics

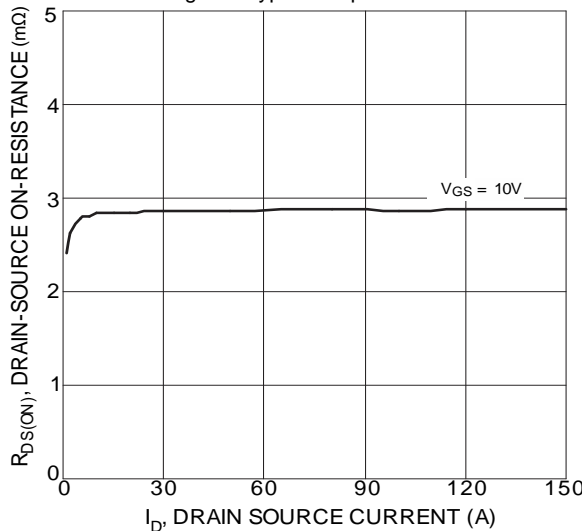


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

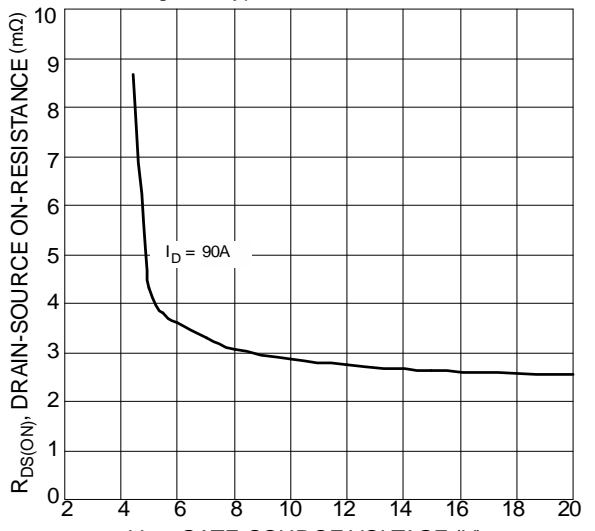


Figure 4 Typical Transfer Characteristic

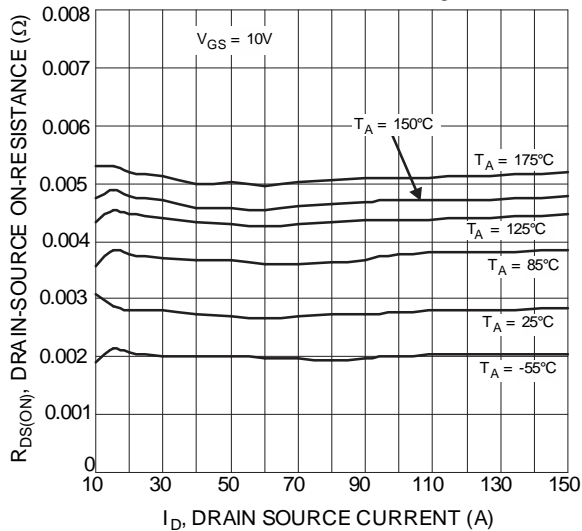


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

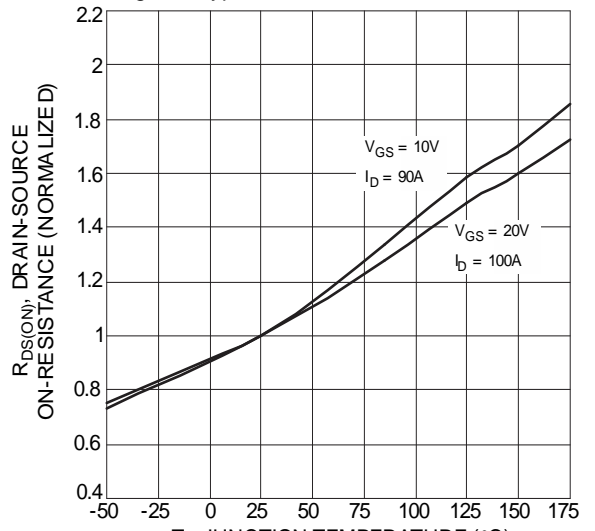


Figure 6 On-Resistance Variation with Temperature

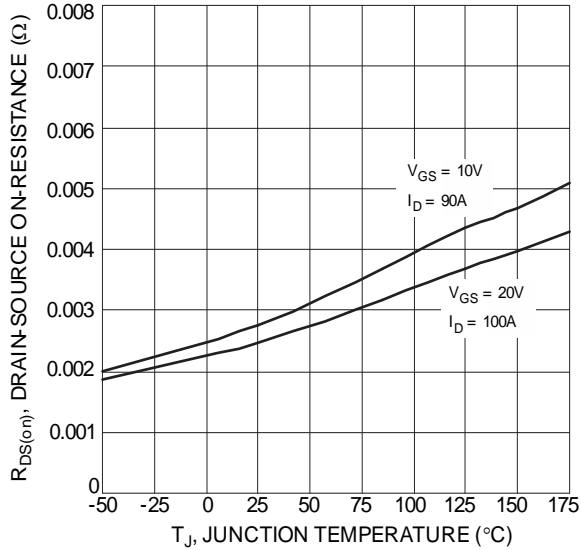


Figure 7 On-Resistance Variation with Temperature

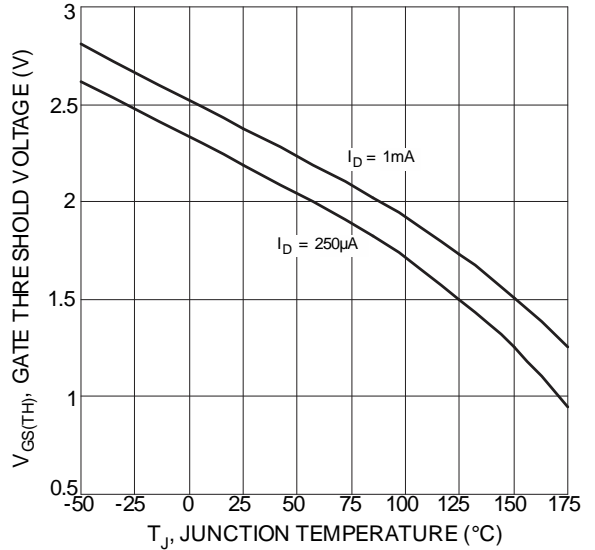


Figure 8 Gate Threshold Variation vs. Temperature

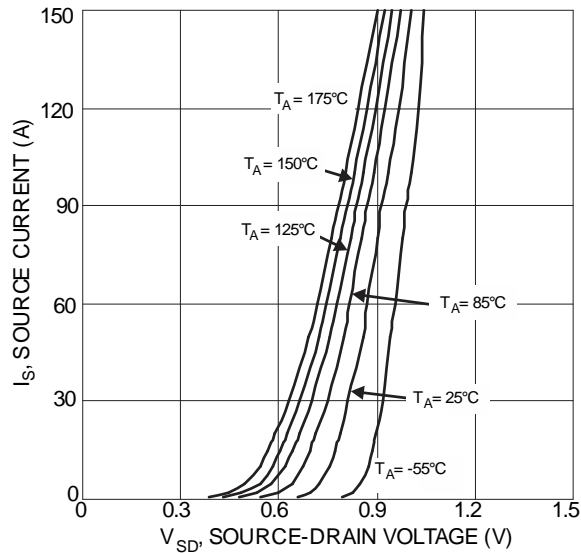


Figure 9 Diode Forward Voltage vs. Current

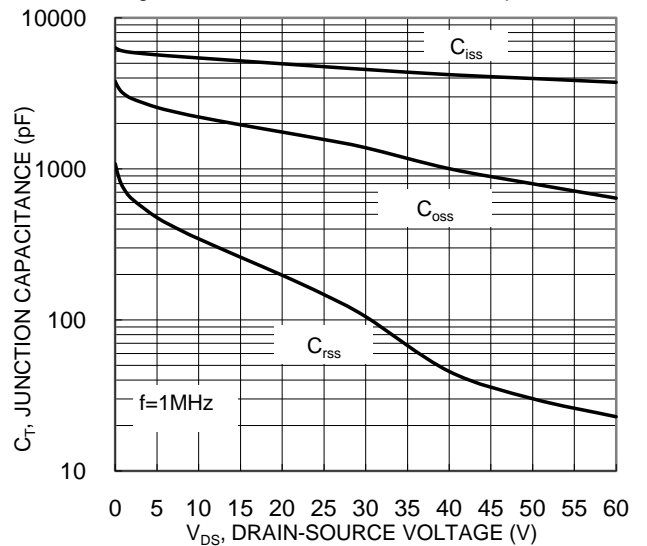


Figure 10. Typical Junction Capacitance

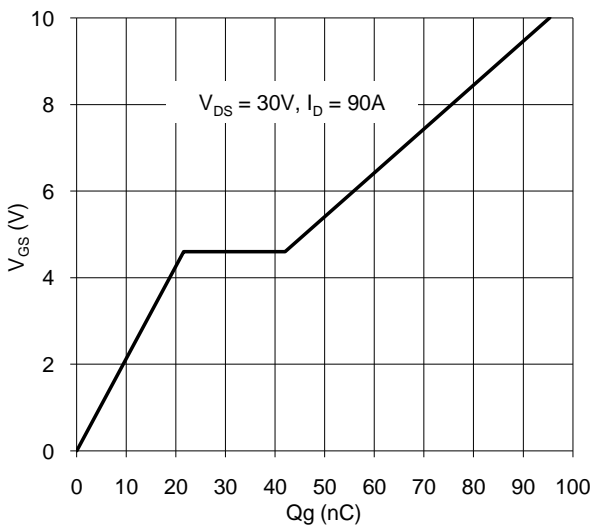


Figure 11. Gate Charge

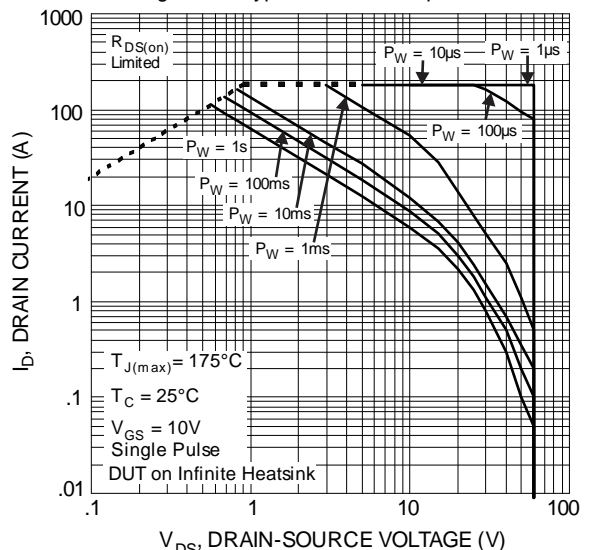


Figure 12 SOA, Safe Operation Area

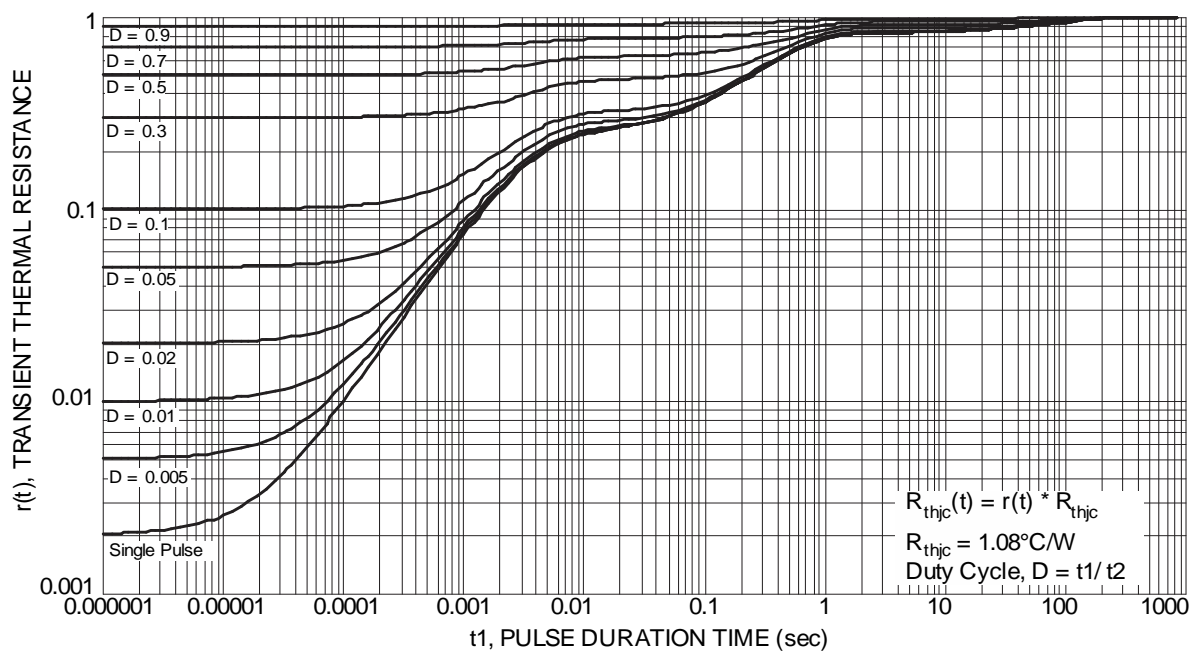
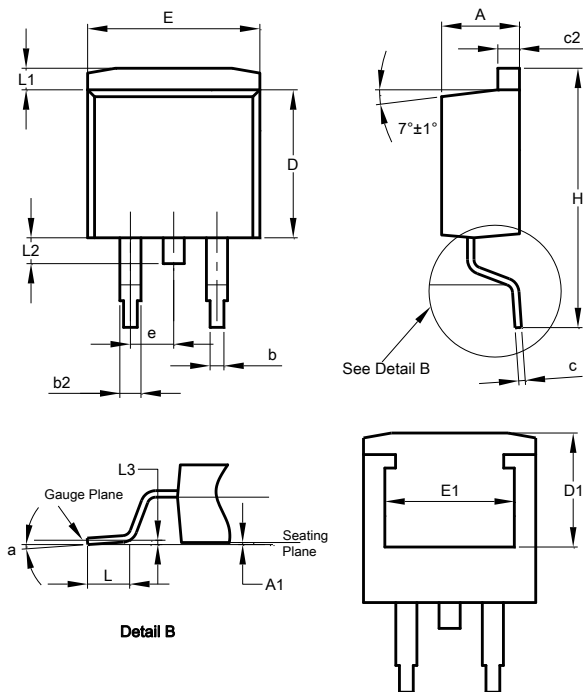


Figure 13 Transient Thermal Resistance

**Package Outline Dimensions**

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

**TO263AB (D2PAK)**

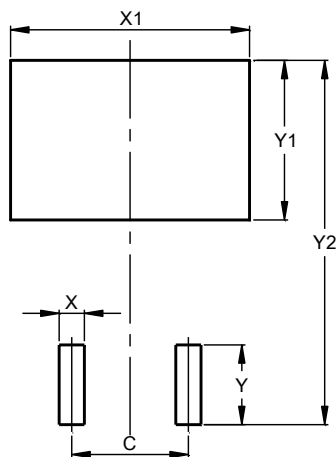


TO263AB (D2PAK)			
Dim	Min	Max	Typ
A	4.07	4.82	—
A1	0.00	0.25	—
b	0.51	0.99	—
b2	1.15	1.77	—
c	0.356	0.73	—
c2	1.143	1.65	—
D	8.39	9.65	—
D1	6.55	6.95	—
e	2.54 TYP		
E	9.66	10.66	—
E1	6.23	8.23	—
H	14.61	15.87	—
L	1.78	2.79	—
L1	—	1.67	—
L2	—	1.77	—
L3	—	—	0.254
a	0°	8°	—
All Dimensions in mm			

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

**TO263AB (D2PAK)**



Dimensions	Value (in mm)
C	5.08
X	1.10
X1	10.41
Y	3.50
Y1	7.01
Y2	15.99

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